

Vishay Siliconix

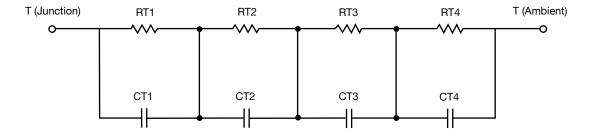
## **R-C Thermal Model Parameters**

#### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

### **R-C THERMAL MODEL FOR TANK CONFIGURATION**



R-C VALUES FOR TANK CONFIGURATION THERMAL RESISTANCE (°C/W)					
RT1	N/A	58.3969m	N/A		
RT2	N/A	583.3954m	N/A		
RT3	N/A	2.8328	N/A		
RT4	N/A	416.1763m	N/A		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CT1	N/A	446.0521u	N/A		
CT2	N/A	241.5574m	N/A		
CT3	N/A	960.6035m	N/A		
CT4	N/A	10.7482m	N/A		

Note

• n/a indicates not applicable

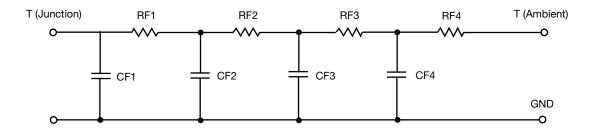
This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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## **R-C THERMAL MODEL FOR FILTER CONFIGURATION**



R-C VALUES FOR FILTER CONFIGURATION THERMAL RESISTANCE (°C/W)					
RF1	N/A	477.8121m	N/A		
RF2	N/A	531.0071m	N/A		
RF3	N/A	361.7111m	N/A		
RF4	N/A	2.5121	N/A		
·	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	N/A	6.5902m	N/A		
CF2	N/A	161.1941m	N/A		
CF3	N/A	53.9755m	N/A		
CF4	N/A	840.2440m	N/A		

Note

• n/a indicates not applicable

# SiHF10N40D\_RC

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SiHF10N40D

4.1

3.0

2.1

1.0

